first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing a substrate between said first and second electrodes;

etching a surface over said substrate with said plasma, and

changing a relative location of the substrate with respect to the plasma in the second direction during the etching,

wherein a gap between said first and second electrodes is 30 mm or less.

2. ~~43~~. (New) The process according to claim 1 ~~42~~ wherein said etching gas comprises nitrogen fluoride.

E1 cont'd

3 ~~44~~. (New) The process according to claim 1 ~~42~~ wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

4 ~~45~~. (New) A process comprising the steps of:

providing first and second electrodes opposed to each other in a reaction chamber, said first electrode having at least one inlet having an opening elongated in a first direction;

introducing an etching gas through said at least one inlet into said reaction chamber;

generating a plasma of said etching gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second

direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing a silicon wafer between said first and second electrodes;

etching a surface over said silicon wafer with said plasma, and

changing a relative location of the silicon wafer with respect to the plasma in the second direction during the etching,

wherein a gap between said first and second electrodes is 30 mm or less.

5 ~~46~~. (New) The process according to claim 4 ~~45~~ wherein said etching gas comprises nitrogen fluoride.

E1 cont'd

6 ~~47~~. (New) The process according to claim 4 ~~45~~ wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

7 ~~48~~. (New) A process comprising the steps of:

providing first and second electrodes opposed to each other in a reaction chamber, said first electrode having at least one inlet having an opening elongated in a first direction;

introducing an ashing gas through said at least one inlet into said reaction chamber;

generating a plasma of said ashing gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

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placing a substrate between said first and second electrodes;

ashing a material on said substrate with said plasma, and

changing a relative location of the substrate with respect to the plasma in the second direction during the ashing,

wherein a gap between said first and second electrodes is 30 mm or less.

8 ~~49~~. (New) The process according to claim 7 ~~48~~ wherein said ashing gas comprises oxygen.

9 ~~50~~. (New) The process according to claim 7 ~~48~~ wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

E1 cont'd

10 ~~51~~. (New) The process according to claim 7 ~~48~~ wherein said material comprises a resist.

11 ~~52~~. (New) The process according to claim 7 ~~48~~ wherein said substrate comprises a glass substrate.

12 ~~53~~. (New) A method of manufacturing a device comprising the steps of:

providing a resist over a substrate;

performing an ion implantation of an impurity using said resist as a mask;

providing first and second electrodes opposed to each other in a reaction chamber, said first electrode having at least one inlet having an opening elongated in a first direction;

introducing an ashing gas through said at least one inlet into said

reaction chamber;

generating a plasma of said ashing gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing said substrate between said first and second electrodes after performing said ion implantation;

ashing said resist with said plasma, and

changing a relative location of the substrate with respect to the plasma in the second direction during the ashing,

wherein a gap between said first and second electrodes is 30 mm or less.

E1 cont'd

13 ~~54~~. (New) The process according to claim 12 ~~53~~ wherein said ashing gas comprises oxygen.

14 ~~55~~. (New) The process according to claim 12 ~~53~~ wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

15 ~~56~~. (New) The process according to claim 12 ~~53~~ wherein said substrate comprises a glass substrate.

16 ~~57~~. (New) The process according to claim 12 ~~53~~ wherein said impurity comprises boron.

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17 ~~58~~. (New) The process according to claim 12 ~~53~~ wherein said device comprises a thin film transistor.

18 ~~59~~. (New) A method of manufacturing a device comprising the steps of:

providing a resist over a substrate;

performing an ion doping of an impurity using said resist as a mask;

providing first and second electrodes opposed to each other in a reaction chamber, said first electrode having at least one inlet having an opening elongated in a first direction;

introducing an ashing gas through said at least one inlet into said reaction chamber;

E1 cont'd

generating a plasma of said ashing gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing said substrate between said first and second electrodes after performing said ion doping;

ashing said resist with said plasma, and

changing a relative location of the substrate with respect to the plasma in the second direction during the ashing,

wherein a gap between said first and second electrodes is 30 mm or less.

19 ~~60~~. (New) The process according to claim 18 ~~59~~ wherein said ashing gas

comprises oxygen.

~~61~~ 20. (New) The process according to claim ~~59~~ 18 wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

~~62~~ 21. (New) The process according to claim ~~59~~ 18 wherein said substrate comprises a glass substrate.

~~63~~ 22. (New) A method of manufacturing a liquid crystal device, comprising the steps of:

providing a resist over a substrate;

performing an ion implantation of an impurity using said resist as a mask;

E cont'd

providing first and second electrodes opposed to each other in a reaction chamber, said first electrode having at least one inlet having an opening elongated in a first direction;

introducing an ashing gas through said at least one inlet into said reaction chamber;

generating a plasma of said ashing gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing said substrate between said first and second electrodes after performing said ion implantation;

ashing said resist over said substrate with said plasma, and

changing a relative location of the substrate with respect to the plasma in the second direction during the ashing,

wherein a gap between said first and second electrodes is 30 mm or less.

23 ~~64~~. (New) The process according to claim 22 ~~63~~ wherein said ashing gas comprises oxygen.

24 ~~65~~. (New) The process according to claim 22 ~~63~~ wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

25 ~~66~~. (New) The process according to claim 22 ~~63~~ wherein said substrate comprises a glass substrate.

E1 cont

26 ~~67~~. (New) The process according to claim 22 ~~63~~ wherein said impurity comprises boron.

27 ~~68~~. (New) The process according to claim 22 ~~63~~ wherein said liquid crystal device includes a thin film transistor.

28 ~~69~~. (New) A method of manufacturing a liquid crystal device comprising the steps of:

providing a resist over a substrate;

performing an ion doping of an impurity using said resist as a mask;

providing first and second electrodes opposed to each other in a reaction

chamber, said first electrode having at least one inlet having an opening elongated in a first direction;

introducing an ashing gas through said at least one inlet into said reaction chamber;

generating a plasma of said ashing gas by applying a voltage between said first and second electrodes wherein at each said at least one inlet said plasma extends from the first electrode toward the second electrode and at each said at least one inlet a cross section of the plasma has a length along the first direction and a width along a second direction perpendicular to the first direction and parallel to the electrodes where the length is longer than the width;

placing said substrate between said first and second electrodes after performing said ion doping;

ashing said resist over said substrate with said plasma, and

changing a relative location of the substrate with respect to the plasma in the second direction during the ashing,

wherein a gap between said first and second electrodes is 30 mm or less.

E cont'd

29 ~~70~~. (New) The process according to claim 28 ~~69~~ wherein said ashing gas comprises oxygen.

30 ~~71~~. (New) The process according to claim 28 ~~69~~ wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

31 ~~72~~. (New) The process according to claim 28 ~~69~~ wherein said substrate comprises a glass substrate.

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